

HiPerFET[™] Power MOSFET

Phaseleg Topology in ISOPLUS i4-PAC™

Preliminary data





 $R_{DSontyp.} = 18 m\Omega$

= 75 A

= 100 V

Features

D25

V_{DSS}

- HiPerFET[™] technology
- low R_{DSon}
 low gate charge for high frequency operation
- unclamped inductive switching (UIS) capability
- dv/dt ruggedness
- fast intrinsic reverse diode
- ISOPLUS i4-PAC[™] package
- isolated back surface
 - low coupling capacity between pins and heatsink
 - enlarged creepage towards heatsink
 - application friendly pinout
 - low inductive current path
 - high reliability
 - industry standard outline
 - UL registered E 72873

Applications

- drives and power supplies
- battery or fuel cell powered
- automotive, industrial vehicle etc.
- · secondary side of mains power supplies

MOSFET T1/T2

Symbol

Conditions

Symbol	Conditions	Maximum F	Maximum Ratings	
V _{DSS}	$T_{vJ} = 25^{\circ}C$ to $150^{\circ}C$	100	V	
V _{GS}		±20	V	
I _{D25} I _{D90}	$T_{c} = 25^{\circ}C$ $T_{c} = 90^{\circ}C$	75 50	A A	
I _{F25} I _{F90}	(body diode) $T_c = 25^{\circ}C$ (body diode) $T_c = 90^{\circ}C$	100 60	A A	
dv/dt	$V_{DS} < V_{DSS}; I_F \le 300A; di_F/dt \le 100A/\mu s; R_G = 2 \Omega$ $T_{VJ} = 150^{\circ}C$	2 5	V/ns	
E _{AR}	$T_c = 25^{\circ}C$	30	mJ	

Characteristic Values $(T_{yy} = 25^{\circ}C)$, unless otherwise specified)

	$(V_{ij}) = 20^{\circ} 0^{\circ}$, amos min.		max.
R _{DSon}	$V_{_{\rm GS}} = 10 \text{ V}; I_{_{\rm D}} = I_{_{\rm D90}}$	18	25 mΩ
V _{GSth}	$V_{DS} = 20 \text{ V}; I_D = 4 \text{ mA}$ 2		4 V
I _{DSS}	$V_{_{DS}} = V_{_{DSS}}; V_{_{GS}} = 0 V; T_{_{VJ}} = 25^{\circ}C$ $T_{_{VJ}} = 125^{\circ}C$	0.25	0.3 mA mA
I _{GSS}	$V_{GS} = \pm 20 \text{ V}; V_{DS} = 0 \text{ V}$		200 nA
Q _g Q _{gs} Q _{gd}	$\begin{cases} V_{GS} = 10 \text{ V}; V_{DS} = 0.5 \bullet V_{DSS}; I_{D} = I_{D90} \end{cases}$	180 35 85	nC nC nC
t _{d(on)} t _r t _{d(off)} t _f	$\begin{cases} V_{GS} = 10 \text{ V}; V_{DS} = 0.5 \bullet V_{DSS} \\ I_{D} = I_{D90}; $	20 60 80 60	ns ns ns ns
V _F	(body diode) $I_F = 75 \text{ A}; V_{GS} = 0 \text{ V}$	1.2	1.5 V
t _{rr}	(body diode) $I_{F} = 37.5$ A; -di/dt = 100A/µs; $V_{DS} = 25$ V	300	ns
R _{thJC} R _{thJH}	with heat transfer paste	0.93	0.5 K/W K/W

IXYS reserves the right to change limits, test conditions and dimensions.

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Component						
Conditions	Maximum Rating					
	-55+150 -55+125	°C ℃				
$I_{ISOL} \le 1 \text{ mA}; 50/60 \text{ Hz}$	2500	V~				
mounting force with clip	20120	Ν				
	Conditions $I_{ISOL} \le 1 \text{ mA}; 50/60 \text{ Hz}$	Conditions Maximum R -55+150 -55+125 I _{ISOL} ≤ 1 mA; 50/60 Hz 2500				

Symbol	Conditions	Characteristic Values		
		min.	typ.	max.
C _p	coupling capacity between shorted pins and mounting tab in the case		40	pF
d _s ,d _A d _s ,d _A	pin - pin pin - backside metal	1.7 5.5		mm mm
Weight			9	g

Dimensions in mm (1 mm = 0.0394")

